

2SK1762

Silicon N Channel MOS FET

REJ03G0969-0200
(Previous: ADE-208-1316)
Rev.2.00
Sep 07, 2005

Application

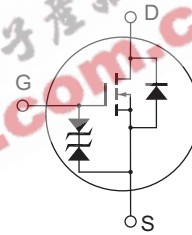
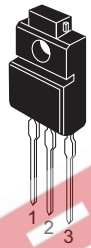
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator, DC-DC converter

Outline

RENESAS Package code: PRSS0003AD-A
(Package name: TO-220FM)



1. Gate
2. Drain
3. Source

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	250	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	12	A
Drain peak current	I _{D(pulse)} * ¹	48	A
Body to drain diode reverse drain current	I _{DR}	12	A
Channel dissipation	P _{ch} * ²	35	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1 %
 2. Value at Tc = 25°C

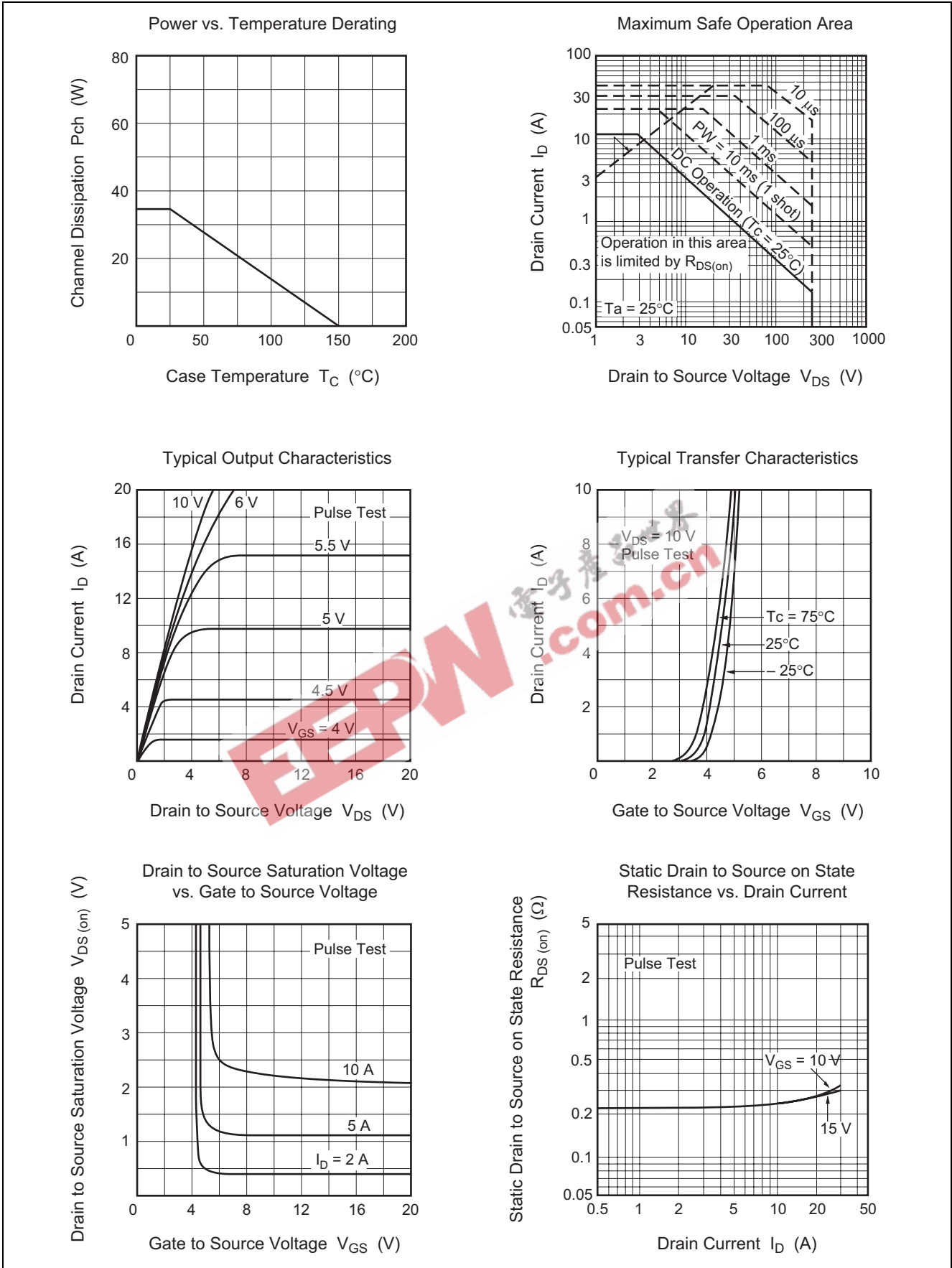
Electrical Characteristics

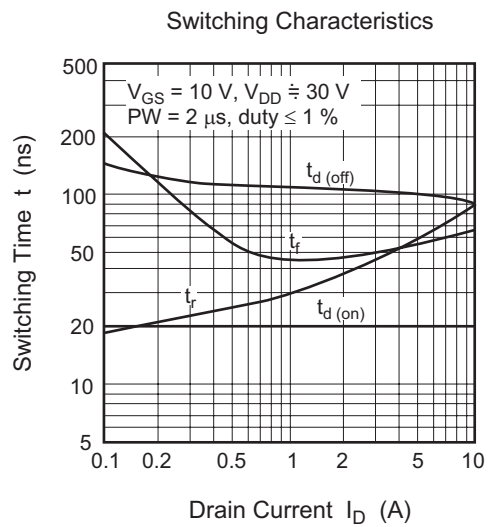
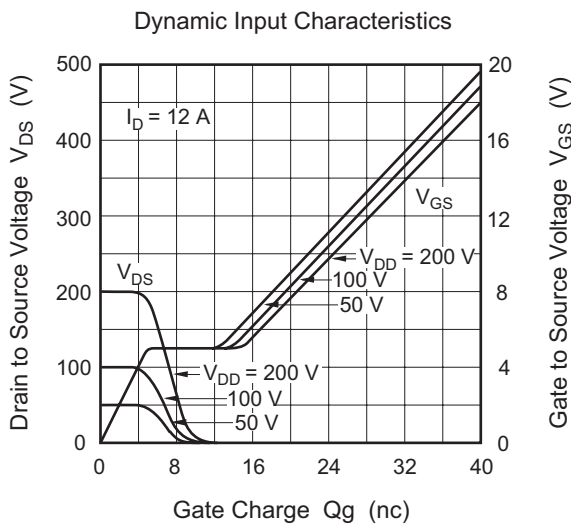
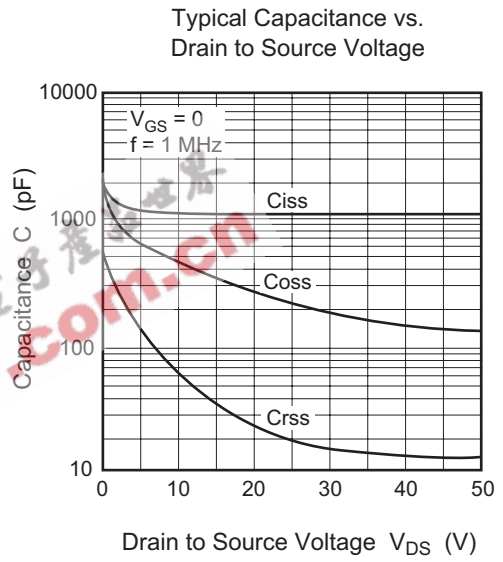
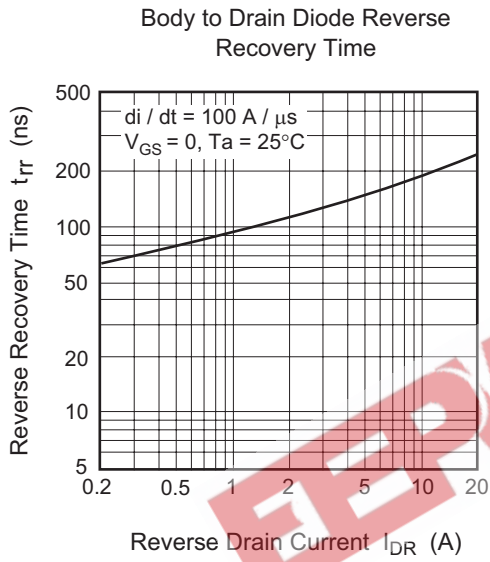
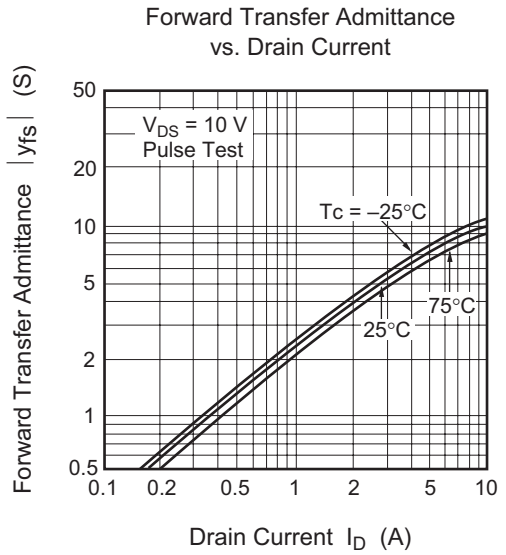
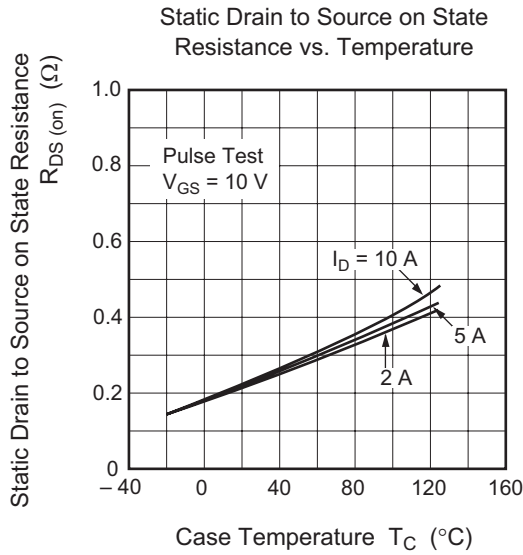
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR)DSS}	250	—	—	V	I _D = 10 mA, V _{GS} = 0
Gate to source breakdown voltage	V _{(BR)GSS}	±30	—	—	V	I _G = ±100 μA, V _{DS} = 0
Gate to source leak current	I _{GSS}	—	—	±10	μA	V _{GS} = ±25 V, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	250	μA	V _{DS} = 200 V, V _{GS} = 0
Gate to source cutoff voltage	V _{GS(off)}	2.0	—	3.0	V	I _D = 1 mA, V _{DS} = 10 V
Static drain to source on state resistance	R _{DS(on)}	—	0.23	0.35	Ω	I _D = 6 A, V _{GS} = 10 V* ³
Forward transfer admittance	y _{fs}	5.0	8.0	—	S	I _D = 6 A, V _{DS} = 10 V* ³
Input capacitance	C _{iss}	—	1100	—	pF	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz
Output capacitance	C _{oss}	—	440	—	pF	
Reverse transfer capacitance	C _{rss}	—	68	—	pF	
Turn-on delay time	t _{d(on)}	—	20	—	ns	I _D = 6 A, V _{GS} = 10 V, R _L = 5 Ω
Rise time	t _r	—	65	—	ns	
Turn-off delay time	t _{d(off)}	—	100	—	ns	
Fall time	t _f	—	44	—	ns	
Body to drain diode forward voltage	V _{DF}	—	1.0	—	V	I _F = 12 A, V _{GS} = 0
Body to drain diode reverse recovery time	t _{rr}	—	200	—	ns	I _F = 12 A, V _{GS} = 0, di _F /dt = 100 A/μs

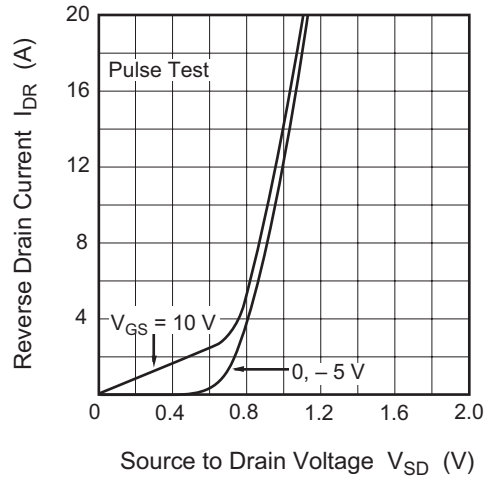
Note: 3. Pulse Test

Main Characteristics

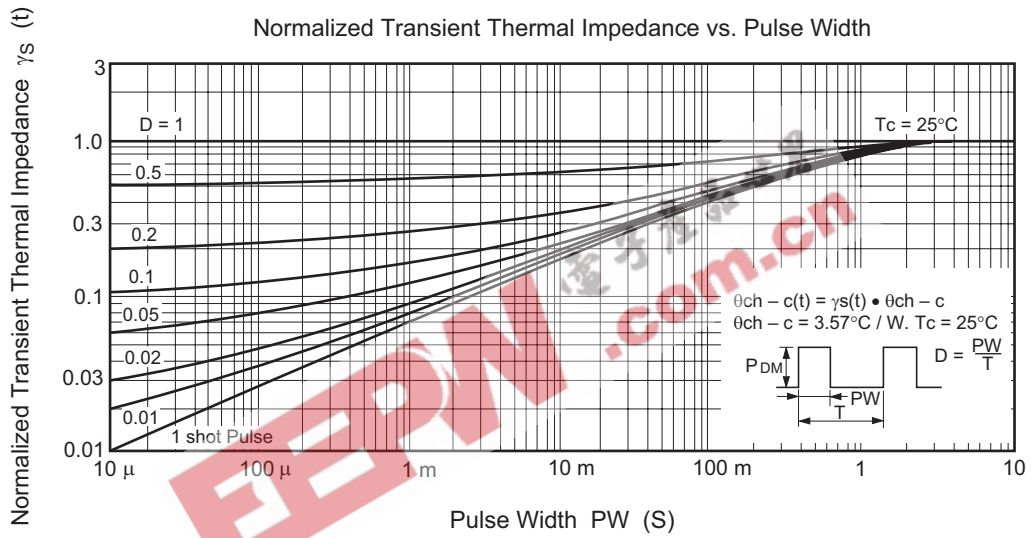




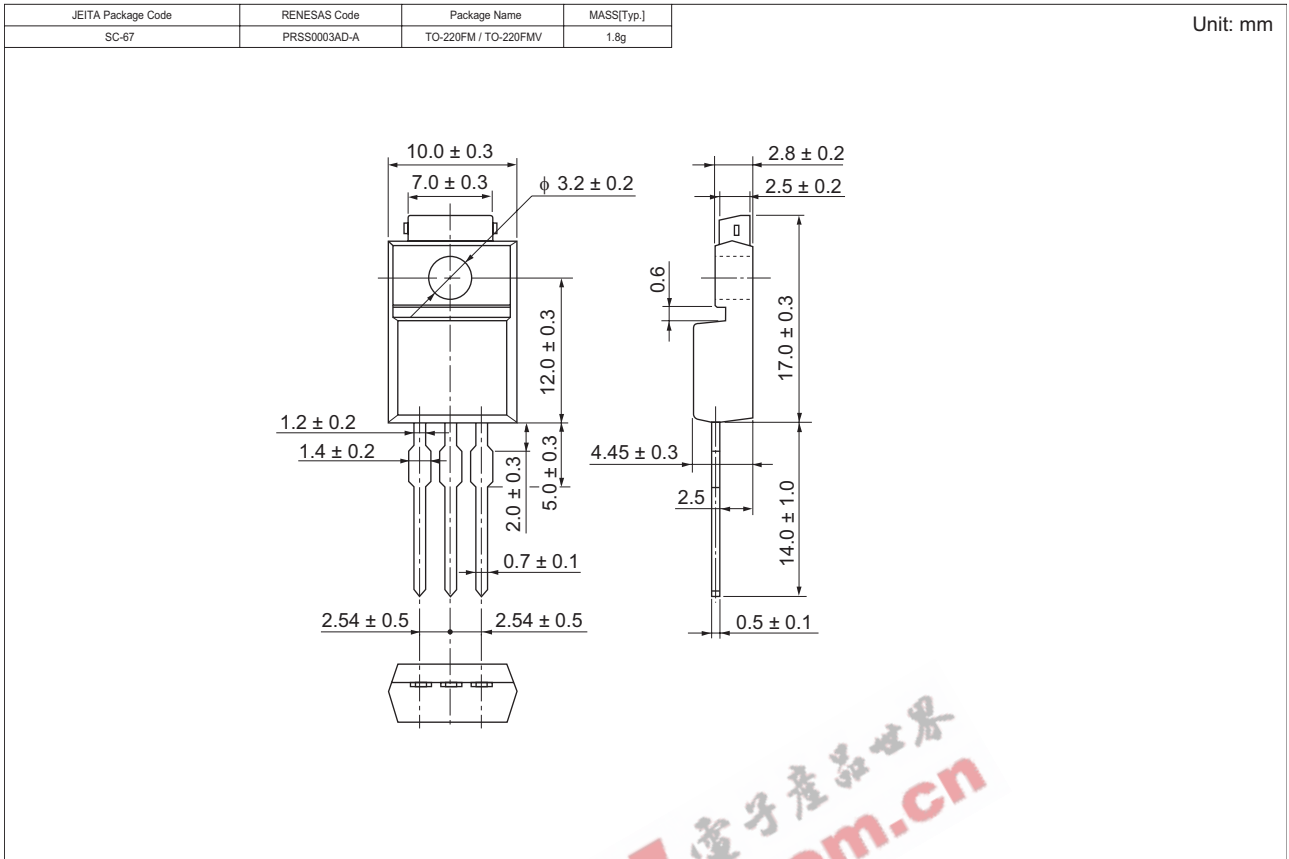
Reverse Drain Current vs. Source to Drain Voltage



Normalized Transient Thermal Impedance vs. Pulse Width



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK1762-E	500 pcs	Box (Sack)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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